Title (en)
AN ACTIVE MATRIX DISPLAY AND A METHOD FOR THRESHOLD VOLTAGE COMPENSATION IN AN ACTIVE MATRIX DISPLAY

Title (de)
AKTIVMATRIXANZEIGE UND VERFAHREN ZUR KONPENSIERUNG VON SCHWELLENSPANNUNG

Title (fr)
ECRAN A MATRICE ACTIVE PROCÉDÉ DE COMPENSATION POUR TENSION DE SEUIL

Publication
EP 3367374 A1 20180829 (EN)

Application
EP 17158476 A 20170228

Priority
EP 17158476 A 20170228

Abstract (en)
A method for threshold voltage compensation in an active matrix display (200) is provided. The display (200) comprises pixels (100), each comprising a drive transistor (102) having a driver gate (104) and a calibration gate (106), a first dataline (110) selectively connected to the driver gate (104), a second dataline (114) selectively connected to the calibration gate (106). The method comprises: driving (402) the display (200) in a calibration measurement mode for measuring a threshold voltage of a pixel (100), wherein the first dataline (110) is connected to the driver gate (104) and the second dataline (114) is connected to the calibration gate (106), and a measurement signal is actively driven to one of the first and the second dataline (110; 114) and a calibration signal is measured on the other of the first and the second dataline (110; 114), determining (404) calibration data based on the measured calibration signal; and driving (406) the display (200) in a calibration refresh mode, wherein the second dataline (114) is connected to the calibration gate (106) of the drive transistor (102), and the determined calibration data is provided on the second dataline (114) to the calibration gate (106) of the drive transistor (102).

IPC 8 full level
G09G 3/3275 (2016.01)

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DOCDB simple family (application)
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